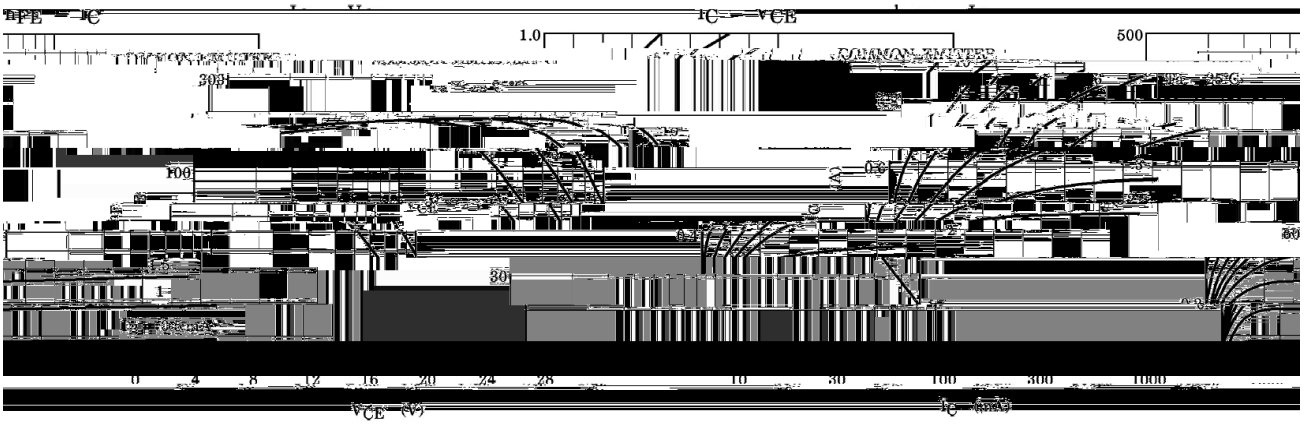
/ Absolute Maximum Ratings(Ta=25)

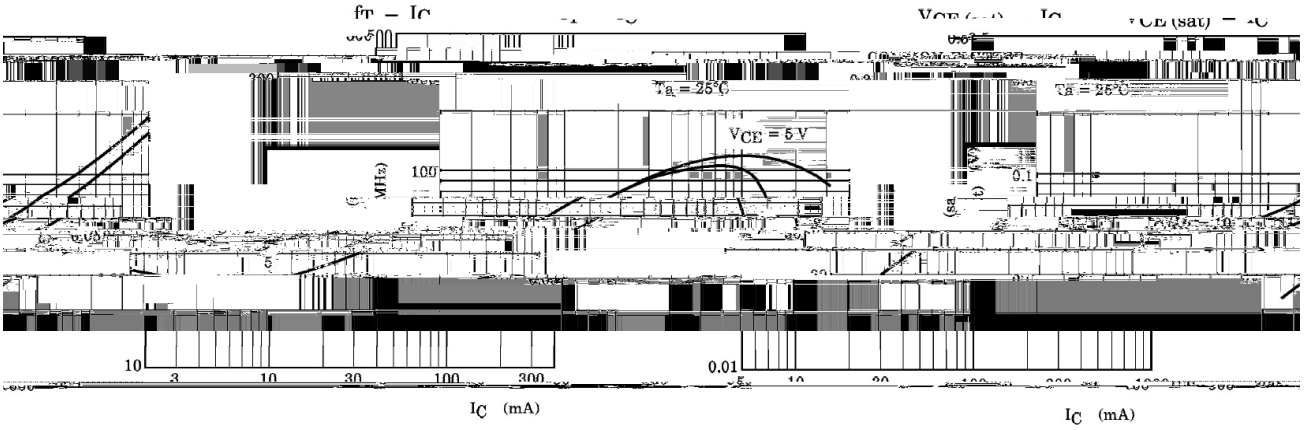
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	160	V
Collector to Emitter Voltage	V_{CEO}	160	V
Emitter to Base Voltage	V_{EBO}	6.0	V
Collector Current (DC)	I_C	1.0	A
Base Current	I_B	0.5	A
Collector Power Dissipation	P_C	900	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

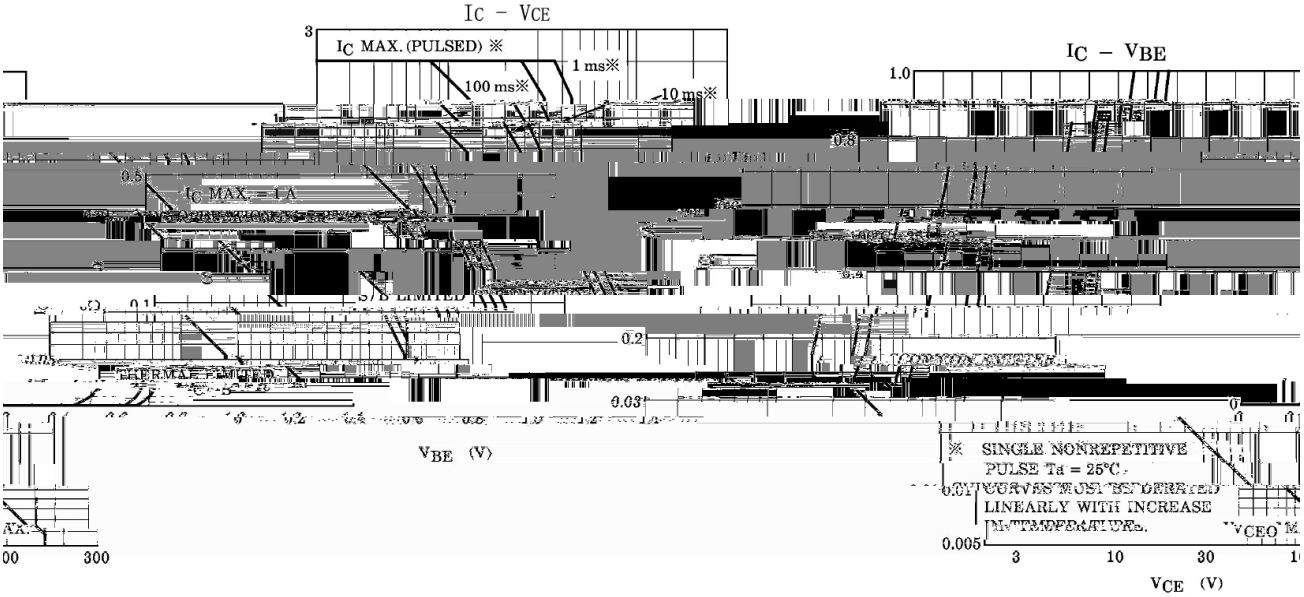
/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=10mA I_B=0	160			V
Collector to Base Breakdown Voltage	V_{CBO}	I_C=100μA I_B=0	160			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=150V I_E=0			1.0	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}=6.0V I_C=0			1.0	μA
DC Current Gain	h_{FE}	V_{CE}=5.0V I_C=200mA	60		320	
Base to Emitter Voltage	V_{BE}	V_{CE}=5.0V I_C=5.0mA	0.45		0.75	V
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=500mA I_B=50mA			1.5	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=500mA I_B=50mA			1.2	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=200mA	20	100		MHz
Collector output capacitance	C_{ob}	V_{CB}=10V I_E=0 f=1.0MHz			20	pF

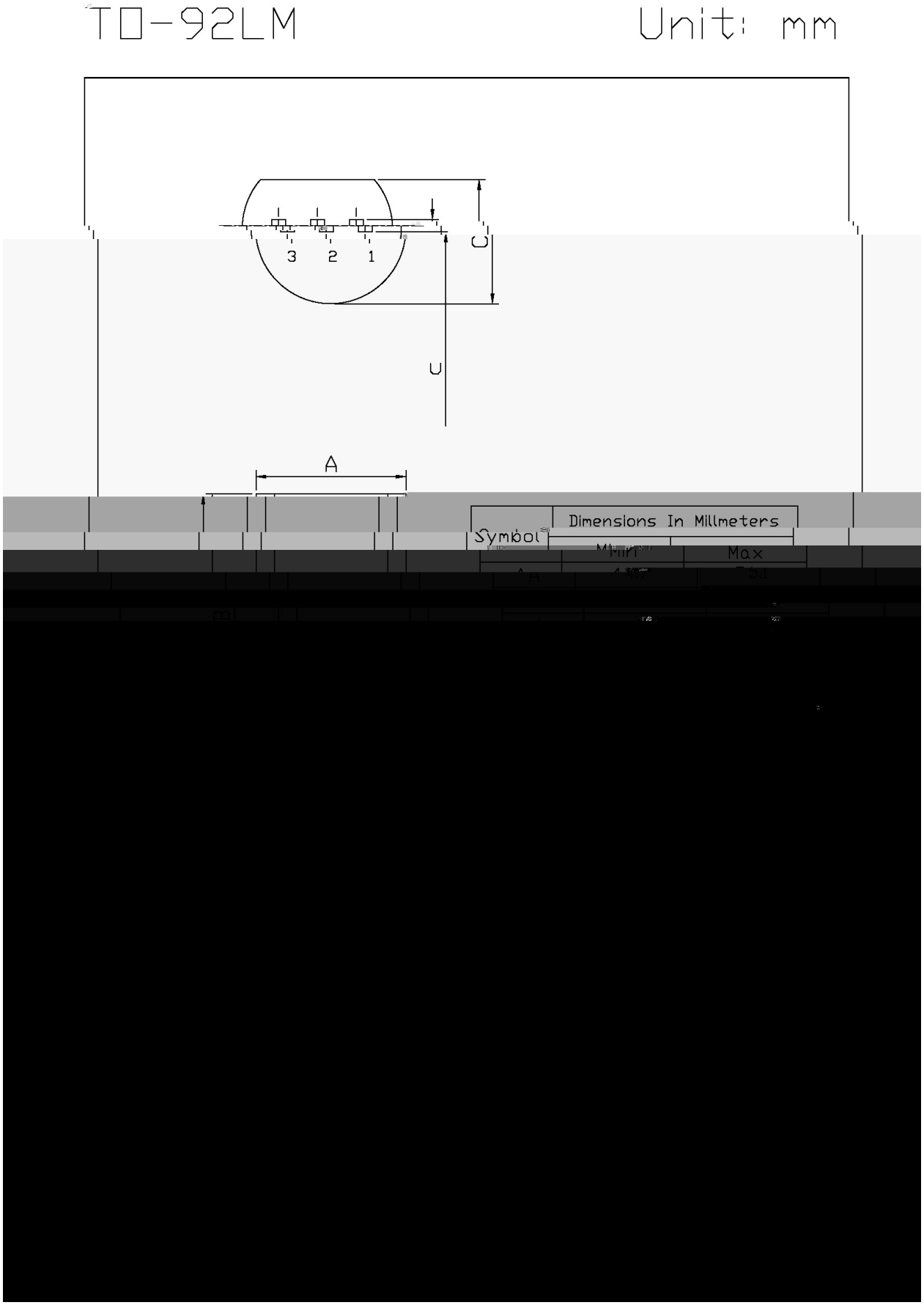
/ Electrical Characteristic Curve

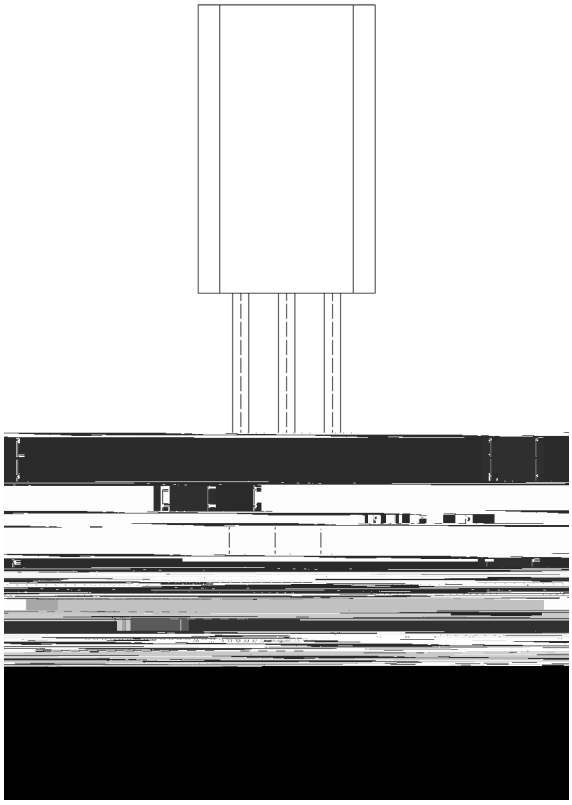




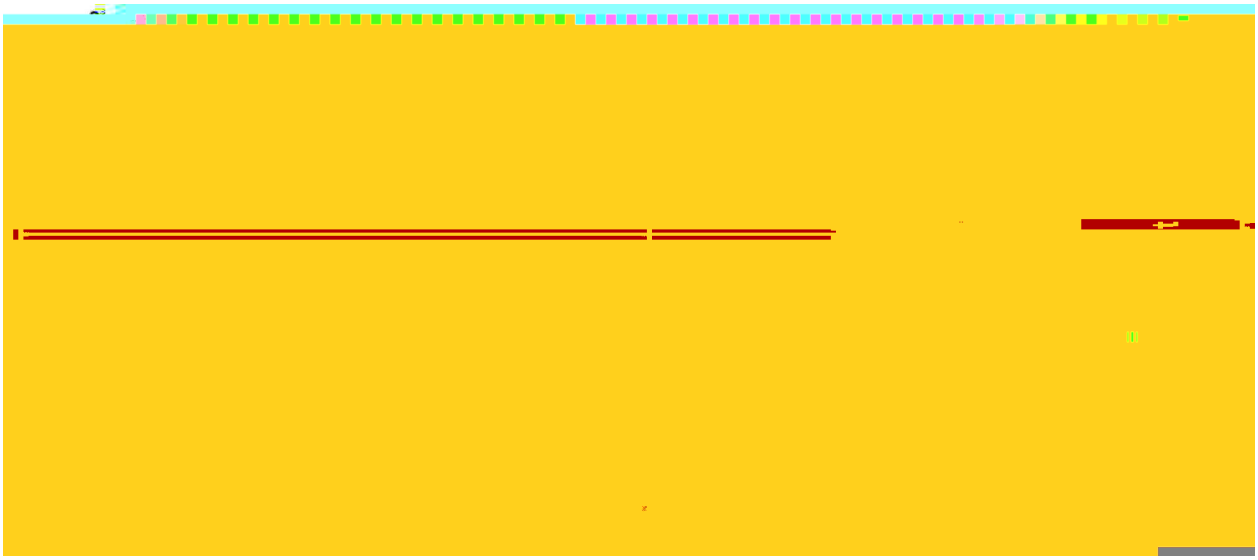


/ Package Dimensions





( ) / Temperature Profile for Dip Soldering(Pb-Free)



			Note:
1	25 150	60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2	255±5	5±0.5sec;	2.Peak Temp.:255±5 , Duration:5±0.5sec.
3	2 10 /sec.		3. Cooling Speed: 2~10 /sec.

/ Resistance to Soldering Heat Test Conditions

270±5	10±1 sec.	Temp.:270±5	Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92LM	1,000	8	8,000	5	40,000	135×190	237×172×102	560×245×195

/ AMMO

Package Type	Units					Dimension	(unit mm3)
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92LM	2,500	1	100	10	25,000	328×230×42	480×346×235 547×407×268

/ Notices